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FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)

Attorney Docket Number: 5308-389

Serial No.: To be determined

10/772882

Applicants: Adam William Saxler

Filing Date: Concurrently herewith

Group: Uknown

Filing Date if

Examiner Initial		Document Number	Date	Name	Class	Subclass
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Application Number	10/772,882	
Filing Date	February 5, 2004	
First Named Inventor	Saxler	
Group Art Unit	2811	
Examiner Name	Jerome Jackson Jr.	
Attorney Docket Number	5308-389	

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Application Number	10/772,882						
Filing Date	February 5, 2004						
First Named Inventor	Saxler						
Group Art Unit	2815	_					
Examiner Name	Jerome Jackson, Jr.						
Attorney Docket Number	5308-389						

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Sheet	3	of	3	Attorney Docket Number	5308-389			

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Attorney Docket Number	5308-389	

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First Named Inventor	Adam Saxler	
Group Art Unit	2815	
Examiner Name	Jerome Jackson, Jr.	
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STATEMENT BY APPLICANT	First Named Inventor	Adam Saxler	
STATEMENT BY APPLICANT IN 2 9 20	Group Art Unit	2815	
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